

Silicon PNP Power Transistors

2SB856

DESCRIPTION

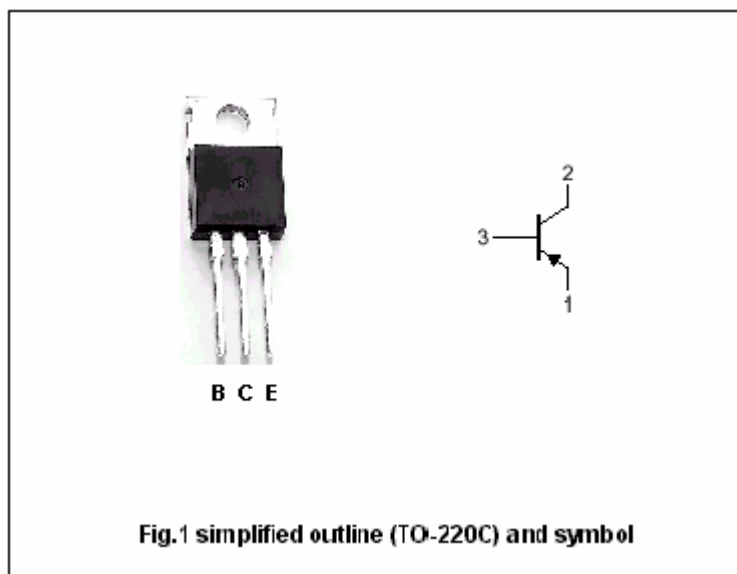
- With TO-220C package
- Low collector saturation voltage

APPLICATIONS

- Low frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_c=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current		-3	A
P_C	Collector power dissipation	$T_c=25^\circ$	25	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-45~150	$^\circ$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; R _{BE} =∞	-50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA; I _E =0	-50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA; I _C =0	-4			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2 A; I _B =-0.2 A			-1.2	V
V _{BE}	Base-emitter voltage	I _C =-1A ; V _{CE} =-4V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-100	μA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-4V	35		200	
h _{FE-2}	DC current gain	I _C =-0.1A ; V _{CE} =-4V	35			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-4V		35		MHz

◆ h_{FE-1} classifications

A	B	C
35-70	60-120	100-200

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PACKAGE OUTLINE

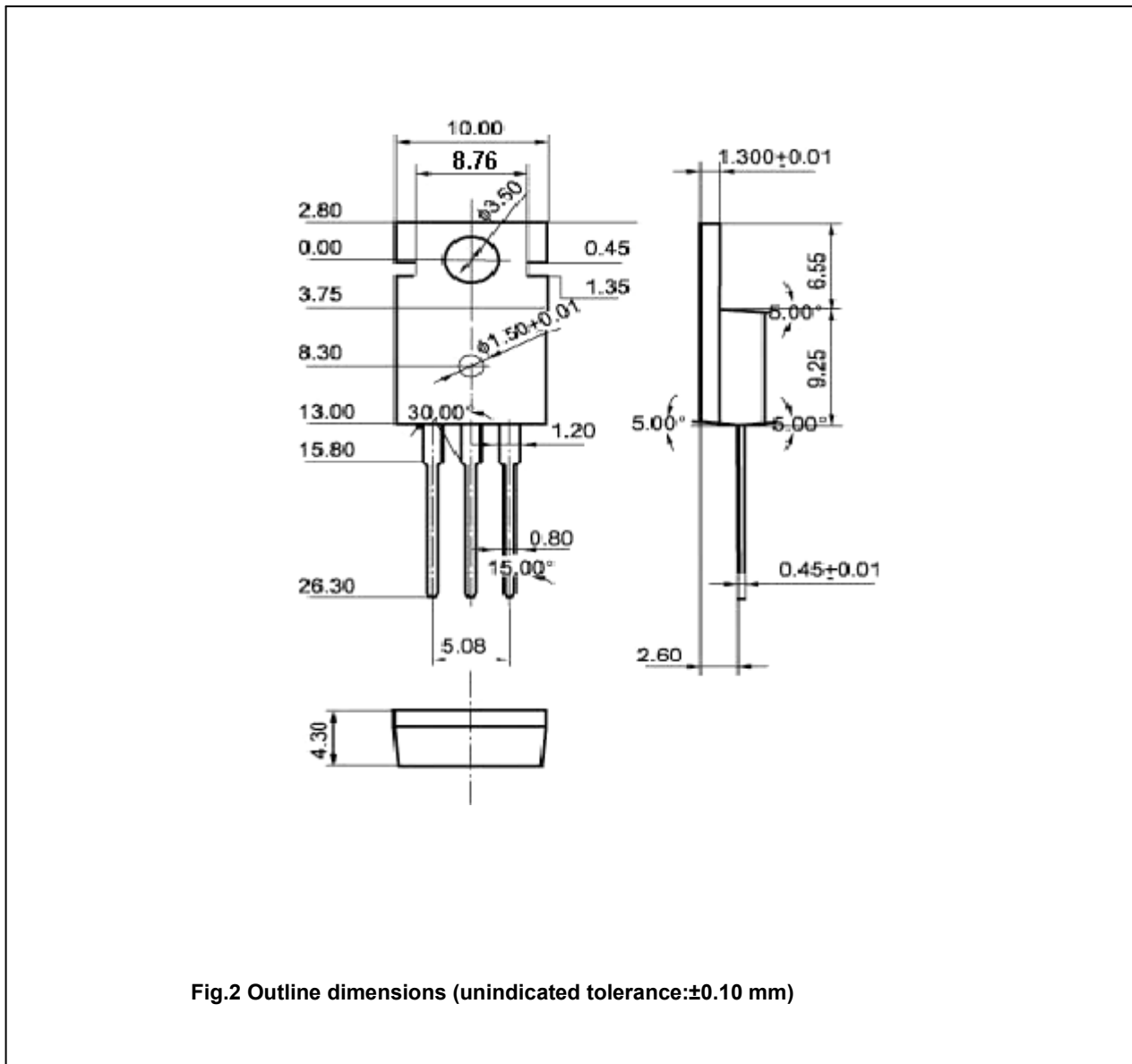


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)